

Yuzo Ohno

List of Publications by Year in descending order

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103
papers

8,567
citations

126858

33
h-index

42364

92
g-index

103
all docs

103
docs citations

103
times ranked

6964
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrical spin injection in a ferromagnetic semiconductor heterostructure. <i>Nature</i> , 1999, 402, 790-792.	13.7	2,315
2	Electric-field control of ferromagnetism. <i>Nature</i> , 2000, 408, 944-946.	13.7	1,904
3	Quantum Hall Effect in Polar Oxide Heterostructures. <i>Science</i> , 2007, 315, 1388-1391.	6.0	531
4	Magnetic Tunnel Junctions for Spintronic Memories and Beyond. <i>IEEE Transactions on Electron Devices</i> , 2007, 54, 991-1002.	1.6	460
5	Spin Relaxation in GaAs(110) Quantum Wells. <i>Physical Review Letters</i> , 1999, 83, 4196-4199.	2.9	389
6	High Mobility Thin Film Transistors with Transparent ZnO Channels. <i>Japanese Journal of Applied Physics</i> , 2003, 42, L347-L349.	0.8	267
7	Observation of the fractional quantum Hall effect in an oxide. <i>Nature Materials</i> , 2010, 9, 889-893.	13.3	258
8	Spontaneous splitting of ferromagnetic (Ga, Mn)As valence band observed by resonant tunneling spectroscopy. <i>Applied Physics Letters</i> , 1998, 73, 363-365.	1.5	147
9	Magnetoresistance effect and interlayer coupling of (Ga, Mn)As trilayer structures. <i>Applied Physics Letters</i> , 2000, 77, 1873.	1.5	143
10	Optical Manipulation of Nuclear Spin by a Two-Dimensional Electron Gas. <i>Physical Review Letters</i> , 2001, 86, 2677-2680.	2.9	142
11	A Spin Esaki Diode. <i>Japanese Journal of Applied Physics</i> , 2001, 40, L1274-L1276.	0.8	125
12	Magnetotransport properties of (Ga,Mn)As investigated at low temperature and high magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 976-980.	1.3	117
13	Phase Transition in the $\nu=2$ Bilayer Quantum Hall State. <i>Physical Review Letters</i> , 1998, 80, 4534-4537.	2.9	104
14	Molecular beam epitaxy of III-V diluted magnetic semiconductor (Ga,Mn)Sb. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 7, 981-985.	1.3	78
15	Generation and control of polarization-entangled photons from GaAs island quantum dots by an electric field. <i>Nature Communications</i> , 2012, 3, 661.	5.8	76
16	Electron mobility exceeding $10^4 \text{ cm}^2/\text{Vs}$ in an AlGaIn/GaN heterostructure grown on a sapphire substrate. <i>Applied Physics Letters</i> , 1999, 74, 3531-3533.	1.5	68
17	Hall magnetometry on a single iron nanoparticle. <i>Applied Physics Letters</i> , 2002, 80, 4644-4646.	1.5	65
18	Relaxation of photoinjected spins during drift transport in GaAs. <i>Applied Physics Letters</i> , 2002, 81, 2788-2790.	1.5	56

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19	Interlayer exchange in (Ga,Mn)As/(Al,Ga)As/(Ga,Mn)As semiconducting ferromagnet/nonmagnet/ferromagnet trilayer structures. Applied Physics Letters, 1998, 73, 2122-2124.	1.5	53
20	Anisotropic electrical spin injection in ferromagnetic semiconductor heterostructures. Applied Physics Letters, 2002, 80, 1598-1600.	1.5	53
21	Spin relaxation in n-modulation doped GaAs/AlGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 36-39.	1.3	51
22	(Ga, Mn)As/GaAs Diluted Magnetic Semiconductor Superlattice Structures Prepared by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1997, 36, L73-L75.	0.8	48
23	Direct imaging of gate-controlled persistent spin helix state in a modulation-doped GaAs/AlGaAs quantum well. Applied Physics Express, 2014, 7, 013001.	1.1	47
24	Carrier Mobility Dependence of Electron Spin Relaxation in GaAs Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, 2549-2551.	0.8	44
25	Electrical spin injection in ferromagnetic/nonmagnetic semiconductor heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 489-492.	1.3	44
26	InAs self-organized quantum dashes grown on GaAs (211)B. Applied Physics Letters, 1997, 70, 2738-2740.	1.5	42
27	Magnetotransport studies of AlGaN/GaN heterostructures grown on sapphire substrates: Effective mass and scattering time. Applied Physics Letters, 2000, 76, 2737-2739.	1.5	42
28	Light emission spectra of AlGaAs/GaAs multiquantum wells induced by scanning tunneling microscope. Applied Physics Letters, 1998, 73, 1544-1546.	1.5	41
29	Faraday rotation of ferromagnetic (Ga, Mn)As. Electronics Letters, 1998, 34, 190.	0.5	37
30	Electron spin relaxation beyond D'yakonov-Perel interaction in GaAs/AlGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 6, 817-820.	1.3	37
31	Spin-dependent phenomena in ferromagnetic/nonmagnetic III-V heterostructures. Solid State Communications, 2001, 119, 281-289.	0.9	36
32	Modulation of Noise in Submicron GaAs/AlGaAs Hall Devices by Gating. Physical Review Letters, 2004, 93, 246602.	2.9	36
33	Control of ferromagnetism in field-effect transistor of a magnetic semiconductor. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 351-355.	1.3	33
34	Valence band barrier at (Ga,Mn)As/GaAs interfaces. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 521-524.	1.3	33
35	Evidence for Ferromagnetic Clusters in the Colossal-Magnetoresistance Material EuB_6 . Physical Review Letters, 2018, 120, 257201.	2.9	33
36	Photoluminescence Study of InAs Quantum Dots and Quantum Dashes Grown on GaAs(211)B. Japanese Journal of Applied Physics, 1998, 37, 1527-1531.	0.8	32

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37	Decomposition of $1/f$ Noise in $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ Hall Devices. <i>Physical Review Letters</i> , 2006, 96, 186601.	2.9	29
38	Multipulse Operation and Optical Detection of Nuclear Spin Coherence in a $\text{GaAs}/\text{AlGaAs}$ Quantum Well. <i>Physical Review Letters</i> , 2008, 101, 207601.	2.9	28
39	Growth and properties of $(\text{Ga},\text{Mn})\text{As}$ films with high Mn concentration. <i>Journal of Applied Physics</i> , 2001, 89, 7024-7026.	1.1	27
40	Magnetotransport properties of $(\text{Ga},\text{Mn})\text{As}$ grown on GaAs A substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 10, 206-209.	1.3	27
41	Zincblende CrSb/GaAs multilayer structures with room-temperature ferromagnetism. <i>Materials Science in Semiconductor Processing</i> , 2003, 6, 507-509.	1.9	24
42	Spin-dependent scattering in semiconducting ferromagnetic $(\text{Ga},\text{Mn})\text{As}$ trilayer structures. <i>Journal of Applied Physics</i> , 2000, 87, 6436-6438.	1.1	22
43	Low-temperature field-effect and magnetotransport properties in a ZnO based heterostructure with atomic-layer-deposited gate dielectric. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	22
44	Strong anisotropic spin dynamics in narrow $n\text{-InGaAs}/\text{AlGaAs}$ (110) quantum wells. <i>Applied Physics Letters</i> , 2005, 87, 171905.	1.5	21
45	Effect of $n\text{-GaAs}$ thickness and doping density on spin injection of $\text{GaMnAs}/n\text{-GaAs}$ Esaki tunnel junction. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 32, 438-441.	1.3	20
46	Single-electron switching in $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ Hall devices. <i>Physical Review B</i> , 2006, 74, .	1.1	20
47	InAs quantum dots and dashes grown on (100), (211)B, and (311)B GaAs substrates. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 672-677.	1.3	18
48	Surfactant effect of Mn on the formation of self-organized InAs nanostructures. <i>Journal of Crystal Growth</i> , 2000, 208, 799-803.	0.7	18
49	Magnetization reversal in elongated Fe nanoparticles. <i>Physical Review B</i> , 2005, 71, .	1.1	17
50	Defect-free etching process for $\text{GaAs}/\text{AlGaAs}$ hetero-nanostructure using chlorine/argon mixed neutral beam. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, 1138-1142.	0.6	17
51	Temperature dependence of electroluminescence and $I\text{-}V$ characteristics of ferromagnetic/non-magnetic semiconductor pn junctions. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2001, 10, 288-291.	1.3	16
52	Coherent Manipulation of Nuclear Spins in Semiconductors with an Electric Field. <i>Applied Physics Express</i> , 2013, 6, 033002.	1.1	15
53	Arsenic flux dependence of InAs nanostructure formation on GaAs (211)B surface. <i>Applied Surface Science</i> , 2000, 166, 413-417.	3.1	14
54	Damage-free top-down processes for fabricating two-dimensional arrays of 7 nm GaAs nanodiscs using bio-templates and neutral beam etching. <i>Nanotechnology</i> , 2011, 22, 365301.	1.3	14

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55	A strong anisotropy of spin dephasing time of quasi-one dimensional electron gas in modulation-doped GaAs/AlGaAs wires. Applied Physics Letters, 2013, 102, .	1.5	13
56	Nanocluster building blocks of artificial square spin ice: Stray-field studies of thermal dynamics. Journal of Applied Physics, 2015, 117, .	1.1	13
57	Anomalous stability of $\hat{1}/2 = 1$ bilayer quantum Hall state. Solid State Communications, 1997, 103, 447-451.	0.9	12
58	Spin-dependent properties of ferromagnetic/nonmagnetic GaAs heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 84, 70-74.	1.7	12
59	Magnetic stray-field studies of a single Cobalt nanoelement as a component of the building blocks of artificial square spin ice. Journal of Magnetism and Magnetic Materials, 2016, 400, 206-212.	1.0	12
60	Mobility dependence of electron spin relaxation time in n-type InGaAs/InAlAs multiple quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2000, 7, 1015-1019.	1.3	11
61	Molecular Beam Epitaxy and Properties of Cr-Doped GaSb. Journal of Superconductivity and Novel Magnetism, 2004, 17, 349-352.	0.5	10
62	Electron spin dynamics in InGaAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 1007-1011.	1.3	9
63	Phototransistors Using Point Contact Structures. Japanese Journal of Applied Physics, 1997, 36, 1955-1957.	0.8	8
64	Effect of barrier width on the performance of quantum well infrared photodetector. Infrared Physics and Technology, 2001, 42, 115-121.	1.3	8
65	Band-tail shape and transport near the metal-insulator transition in Si-doped $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"> \langle \text{mml:mrow} \langle \text{mml:msub} \langle \text{mml:mrow} \langle \text{mml:mtext} \text{Al} \langle \text{mml:mtext} \rangle \langle \text{mml:mrow} \langle \text{mml:mn} \langle \text{mml:mtext} \rangle \langle \text{mml:mtext} \rangle \rangle \rangle \rangle \rangle \langle \text{mml:mn} \langle \text{mml:mtext} \rangle \langle \text{mml:mtext} \rangle \rangle \rangle \rangle \rangle$. Physical Review B, 2010, 82, .	1.1	8
66	Magnetization reversal of iron nanoparticles studied by submicron Hall magnetometry. Journal of Applied Physics, 2003, 93, 7912-7914.	1.1	7
67	Direct Observation of Electron Jet from a Point Contact. Japanese Journal of Applied Physics, 1996, 35, 1151-1153.	0.8	6
68	Spin degree of freedom in ferromagnetic semiconductor heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 104-110.	1.3	6
69	Direct mapping of photoexcited local spins in a modulation-doped GaAs/AlGaAs wires. Japanese Journal of Applied Physics, 2014, 53, 04EM04.	0.8	6
70	Surface-mediated spin dynamics probed by optical-pump-probe scanning tunneling microscopy. Physical Chemistry Chemical Physics, 2019, 21, 7256-7260.	1.3	6
71	Surface morphologies of III-V based magnetic semiconductor (Ga,Mn)As grown by molecular beam epitaxy. Applied Surface Science, 2000, 166, 242-246.	3.1	5
72	Properties of (Ga,Mn)As/(Al,Ga)As/(Ga,Mn)As magnetic trilayer structures. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 278-282.	1.3	5

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73	0.7 anomaly and magnetotransport of disordered quantum wires. <i>Europhysics Letters</i> , 2008, 82, 27003.	0.7	4
74	Detection and measurement of electroreflectance on quantum cascade laser device using Fourier transform infrared microscope. <i>Applied Physics Letters</i> , 2013, 103, 231106.	1.5	4
75	Complex switching behavior of magnetostatically coupled single-domain nanomagnets probed by micro-Hall magnetometry. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	4
76	Zero-field spin precession dynamics of high-mobility two-dimensional electron gas in persistent spin helix regime. <i>Physical Review B</i> , 2020, 101, .	1.1	4
77	A few-electron vertical In _{0.56} Ga _{0.44} As quantum dot with an insulating gate. <i>Applied Physics Letters</i> , 2007, 91, 232101.	1.5	3
78	Optical detection of zero-field spin precession of high mobility two-dimensional electron gas in a gated GaAs/AlGaAs quantum well. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 2698-2701.	1.3	3
79	Systematic study of surface morphology, photoluminescence efficiency, and spin-detection sensitivity in (110)-oriented GaAs/AlGaAs quantum wells. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 113001.	0.8	3
80	Room-temperature spin-orbit magnetic fields in slightly misoriented (110) InGaAs/InAlAs multiple quantum wells. <i>Applied Physics Letters</i> , 2021, 119, 032405.	1.5	3
81	Room-temperature spin relaxation in a (110)-oriented GaAs/AlGaAs superlattice with tunnel-coupled quantum wells. <i>Applied Physics Express</i> , 2020, 13, 123003.	1.1	3
82	Photoluminescence from point contact structure – Direct observation of electron flow. <i>Physica B: Condensed Matter</i> , 1996, 227, 77-81.	1.3	2
83	Intersubband exchange interaction induced by optically excited electron spins in GaAs/AlGaAs quantum wells. <i>Applied Physics Letters</i> , 2009, 94, 162104.	1.5	2
84	Width and temperature dependence of lithography-induced magnetic anisotropy in (Ga,Mn)As wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 2685-2689.	1.3	2
85	Photocurrent Measurements on a Quantum Cascade Laser Device by Fourier Transform Infrared Microscope. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 06FE15.	0.8	2
86	Strain dependence of nuclear spin coherence in a (110)GaAs/AlGaAs quantum well. <i>Japanese Journal of Applied Physics</i> , 2014, 53, 093001.	0.8	2
87	Vertical electric field induced suppression of fine structure splitting of excited state excitons in a single GaAs/AlGaAs island quantum dots. <i>Applied Physics Letters</i> , 2015, 107, 123102.	1.5	2
88	Growth condition dependence of photoluminescence polarization in (100) GaAs/AlGaAs quantum wells at room temperature. <i>Journal of Applied Physics</i> , 2015, 118, 083901.	1.1	2
89	Suppression of resonant tunneling in a coupled quantum well. <i>Surface Science</i> , 1996, 361-362, 142-145.	0.8	1
90	Well-width dependence of bound to quasi-bound intersubband transition in GaAs quantum wells with multi-quantum barriers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 1998, 2, 200-203.	1.3	1

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91	MOCVD Growth and Transport Investigation of Two-Dimensional Electron Gas in AlGaIn/GaN Heterostructures on Sapphire Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 1999, 216, 743-748.	0.7	1
92	Low-frequency noise in submicron GaAs/Al _x Ga _{1-x} As Hall devices. <i>Journal of Magnetism and Magnetic Materials</i> , 2005, 290-291, 1161-1164.	1.0	1
93	Detection of local electron and nuclear spin dynamics by time-resolved Kerr microscopy. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010, 42, 2702-2706.	1.3	1
94	Magnetic Field Dependence of Quadrupolar Splitting and Nuclear Spin Coherence Time in a Strained (110) GaAs Quantum Well. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DM03.	0.8	1
95	Vertical-Electrical-Field-Induced Control of the Exciton Fine Structure Splitting in GaAs Island Quantum Dots for the Generation of Polarization-Entangled Photons. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 06FE14.	0.8	1
96	Impacts of Crystal Quality on Carrier Recombination and Spin Dynamics in (110)-Oriented GaAs/AlGaAs Multiple Quantum Wells at Room Temperature. <i>Micromachines</i> , 2021, 12, 1112.	1.4	1
97	Spatiotemporal spin dynamics of two-dimensional electron gas with ballistic motion in persistent spin helix state. <i>Physical Review B</i> , 2022, 105, .	1.1	1
98	$\hat{\nu}/2=1$ bilayer quantum Hall state at arbitrary electron distribution in a double quantum well. <i>Solid-State Electronics</i> , 1998, 42, 1183-1185.	0.8	0
99	Etched-backgate field-effect transistor structure for magnetotunneling study of low-dimensional electron systems. <i>Solid-State Electronics</i> , 1998, 42, 1187-1190.	0.8	0
100	Bilayer $\hat{\nu}/2=2$ quantum Hall state in parallel high magnetic field. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 615-618.	1.3	0
101	Fabrication of a few-electron In _{0.56} Ga _{0.44} As vertical quantum dot with an Al ₂ O ₃ gate insulator. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1930-1932.	1.3	0
102	Damage-free top-down processes for fabricating two-dimensional array of sub-10-nanometer GaAs nanodiscs using bio-template and neutral beam etching for intermediate band solar cell applications. , 2011, , .		0
103	Simultaneous extraction of Rashba and Dresselhaus spin-orbit coefficients in GaAs/AlGaAs (110) two-dimensional electron gas. , 2019, , .		0